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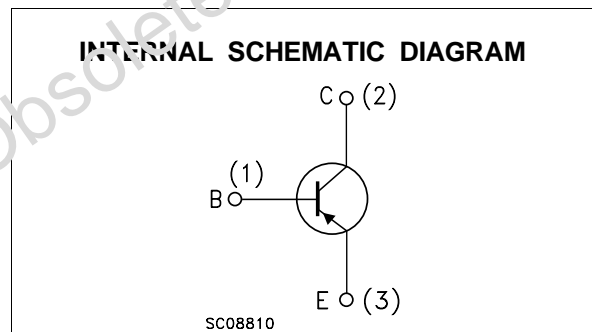
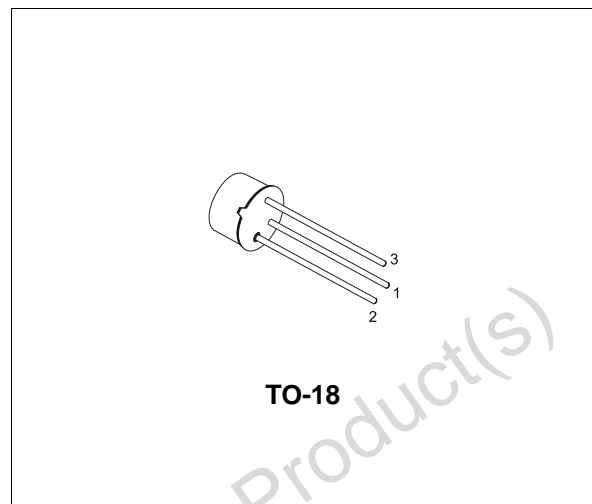
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EPITAXIAL PLANAR NPN

■ HIGH VOLTAGE GENERAL PURPOSE

DESCRIPTION

The 2N790A is a silicon Planar Epitaxial NPN transistor in Jedec TO-18 metal case. It is suitable for a wide variety of amplifier and switching applications.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage ($I_E = 0$) | 120 | V |
| V_{CEO} | Collector-Emitter Voltage ($I_B = 0$) | 80 | V |
| V_{EBO} | Emitter-Base Voltage ($I_C = 0$) | 7 | V |
| I_C | Collector Current | 500 | mA |
| P_{tot} | Total Dissipation at $T_{amb} \leq 25\text{ }^\circ\text{C}$ at $T_C \leq 25\text{ }^\circ\text{C}$ | 0.5 | W |
| | | 1.8 | W |
| T_{stg} | Storage Temperature | -55 to 175 | $^\circ\text{C}$ |
| T_j | Max. Operating Junction Temperature | 175 | $^\circ\text{C}$ |

2N720A

THERMAL DATA

| | | | | |
|-----------------------|-------------------------------------|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-Case | Max | 83.3 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-Ambient | Max | 300 | °C/W |

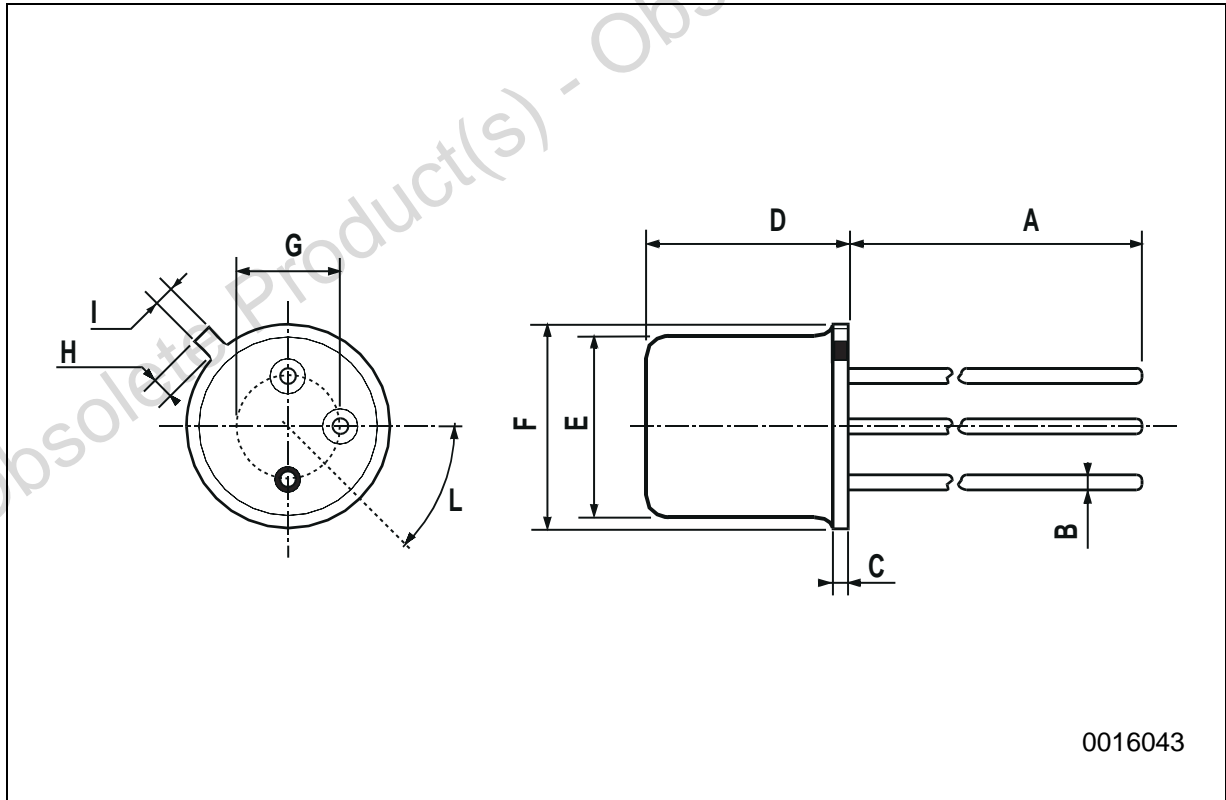
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------|--|--|--|----------------|------------|--------|
| I _{CBO} | Collector Cut-off Current (I _E = 0) | V _{CB} = 90 V | | | 10 | nA |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage (I _E = 0) | I _C = 100 μA | 120 | | | V |
| V _{(BR)CEO*} | Collector-Emitter Breakdown Voltage (I _B = 0) | I _C = 30 mA | 80 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage (I _C = 0) | I _E = 100 μA | 7 | | | V |
| I _{EBO} | Emitter Cut-off Current (I _E = 0) | V _{EB} = 5 V | | | 10 | nA |
| V _{CE(sat)*} | Collector-Emitter Saturation Voltage | I _C = 50 mA I _C = 150 mA | I _B = 5 mA I _B = 15 mA | | 1.2 5 | V V |
| V _{BE(sat)*} | Base-Emitter Saturation Voltage | I _C = 50 mA I _C = 150 mA | I _B = 5 mA I _B = 15 mA | | 0.9 1.3 | V V |
| h _{FE*} | DC Current Gain | I _C = 100 μA I _C = 10 mA I _C = 150 mA | V _{CE} = 10 V V _{CE} = 10 V V _{CE} = 10 V | 20 35 40 | 120 | |
| h _{fe*} | Small Signal Current Gain | I _C = 50 mA f = 20 MHz | V _{CE} = 10 V | 2.5 | | |
| C _{CB0} | Collector-Base Capacitance | I _E = 0 V _{CB} = 10 V f = 1 MHz | | | 15 | pF |
| C _{EBO} | Emitter-Base Capacitance | I _C = 0 V _{EB} = 0.5 V f = 1 MHz | | | 85 | pF |

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1 %

TO-18 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | 12.7 | | | 0.500 | |
| B | | | 0.49 | | | 0.019 |
| D | | | 5.3 | | | 0.208 |
| E | | | 4.9 | | | 0.193 |
| F | | | 5.8 | | | 0.228 |
| G | 2.54 | | | 0.100 | | |
| H | | | 1.2 | | | 0.047 |
| I | | | 1.16 | | | 0.045 |
| L | 45° | | | 45° | | |



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